NTST20U100CT, NTSB20U100CT-1G, NTSJ20U100CTG, NTSB20U100CTG

ON Semiconductor®

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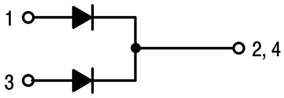
Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low V_F = 0.50 V at I_F = 5 A

PIN CONNECTIONS



Features

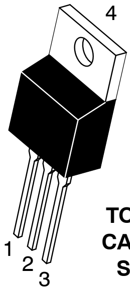
- Fine Lithography Trench−based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb−Free and Halide−Free Packages are Available

Typical Applications

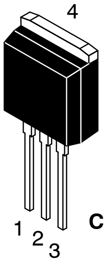
- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC−DC Converters
- Freewheeling and OR−ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

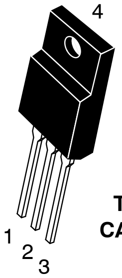
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94−0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



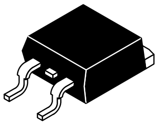
TO−220AB
CASE 221A
STYLE 6



I2PAK
CASE 418D
STYLE 3



TO−220FP
CASE 221AH



D2PAK
CASE 418B

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R, T_C = 130°C) Per device Per diode	$I_{F(AV)}$	 20 10	A
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz, T_C = 125°C) Per device Per diode	I_{FRM}	 40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	A
Operating Junction Temperature	T_J	−40 to +150	°C
Storage Temperature	T_{stg}	−40 to +150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rating	Symbol	NTST20U100CTG, NTSB20U100CT−1G	NTSB20U100CTG	NTSJ20U100CTG	Unit
Maximum Thermal Resistance per Diode Junction−to−Case Junction−to−Ambient	 $R_{\theta JC}$ $R_{\theta JA}$	 2.5 70	 1.24 46.7	 4.20 105	 °C/W °C/W

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	v_F			V
(I_F = 5 A, T_J = 25°C)		0.55	–	
(I_F = 10 A, T_J = 25°C)		0.65	0.79	
(I_F = 5 A, T_J = 125°C)		0.50	–	
(I_F = 10 A, T_J = 125°C)		0.58	0.68	
Maximum Instantaneous Reverse Current (Note 1)	I_R			
(V_R = 70 V, T_J = 25°C)		17	–	μA
(V_R = 70 V, T_J = 125°C)		5.3	–	mA
(Rated dc Voltage, T_J = 25°C)		–	800	μA
(Rated dc Voltage, T_J = 125°C)		12	25	mA

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISITICS

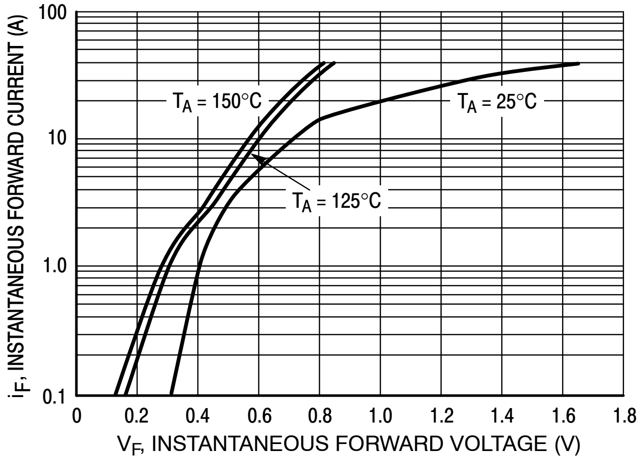


Figure 1. Typical Instantaneous Forward Characteristics

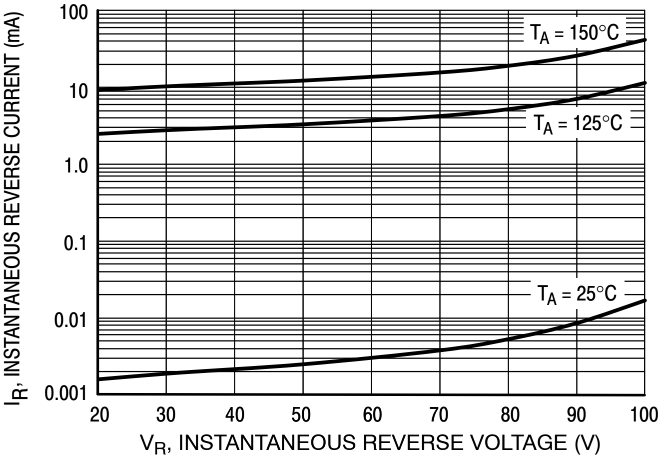


Figure 2. Typical Reverse Characteristics

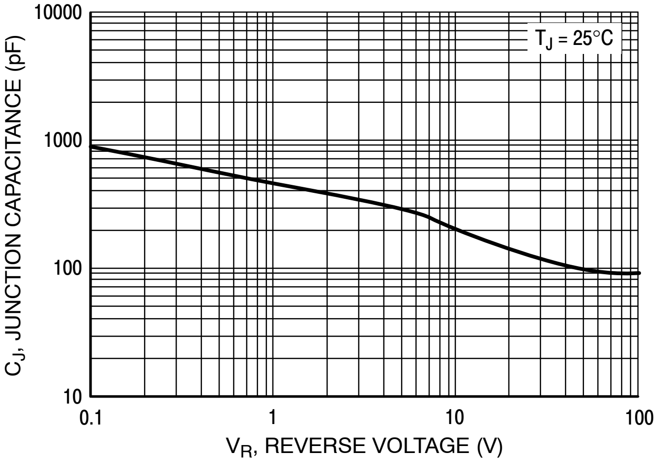


Figure 3. Typical Junction Capacitance

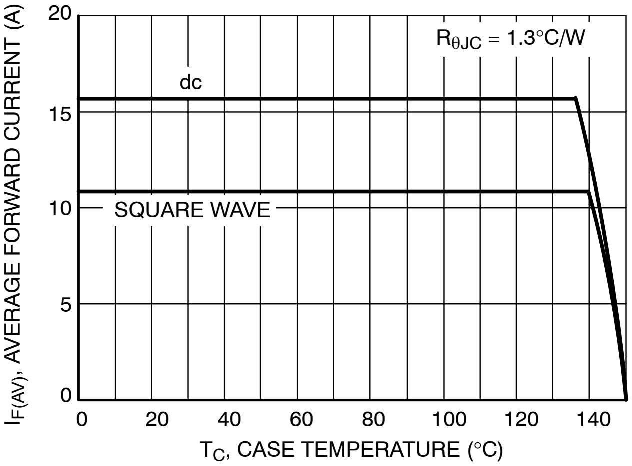


Figure 4. Current Derating per Leg

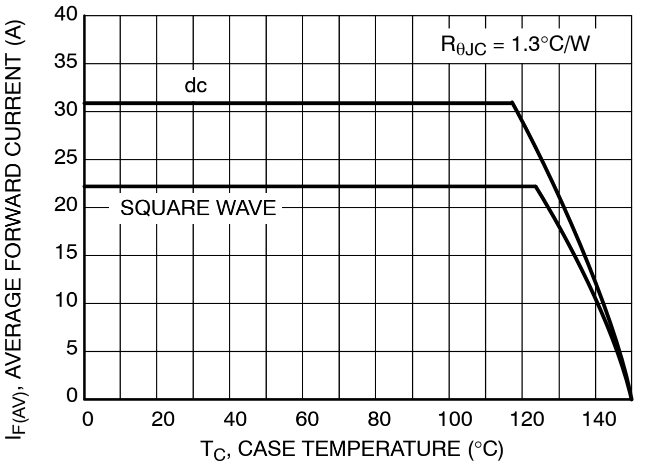


Figure 5. Current Derating

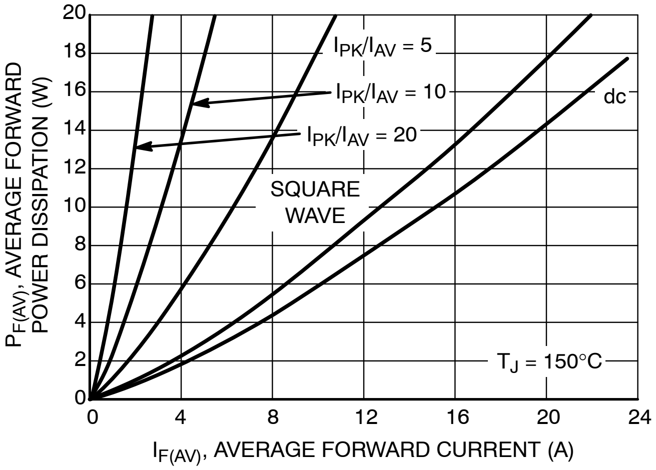


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISITICS

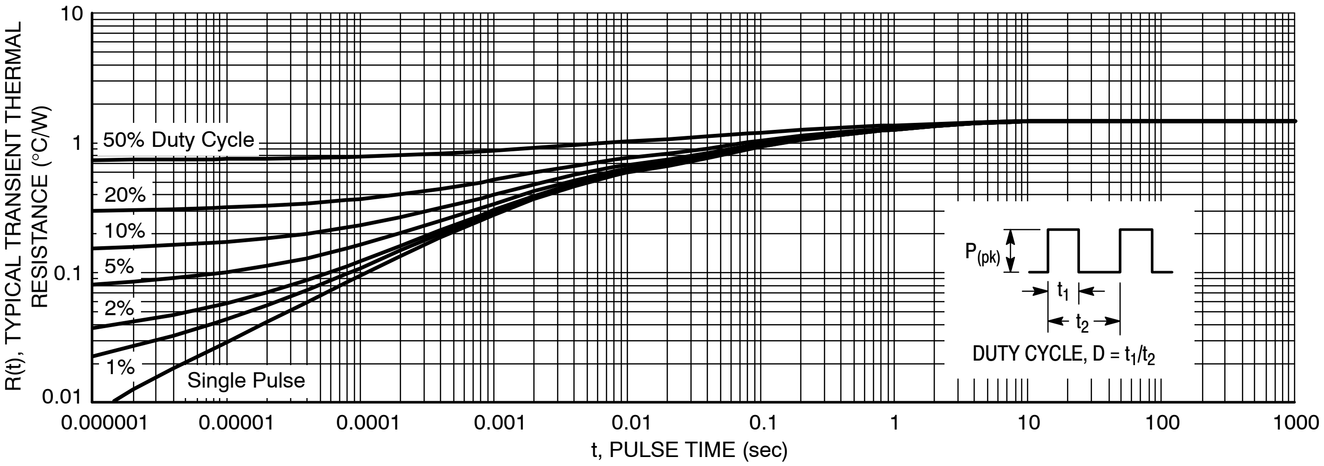


Figure 7. Typical Transient Thermal Response for NTST20U100CT and NTSB20U100CT−1G

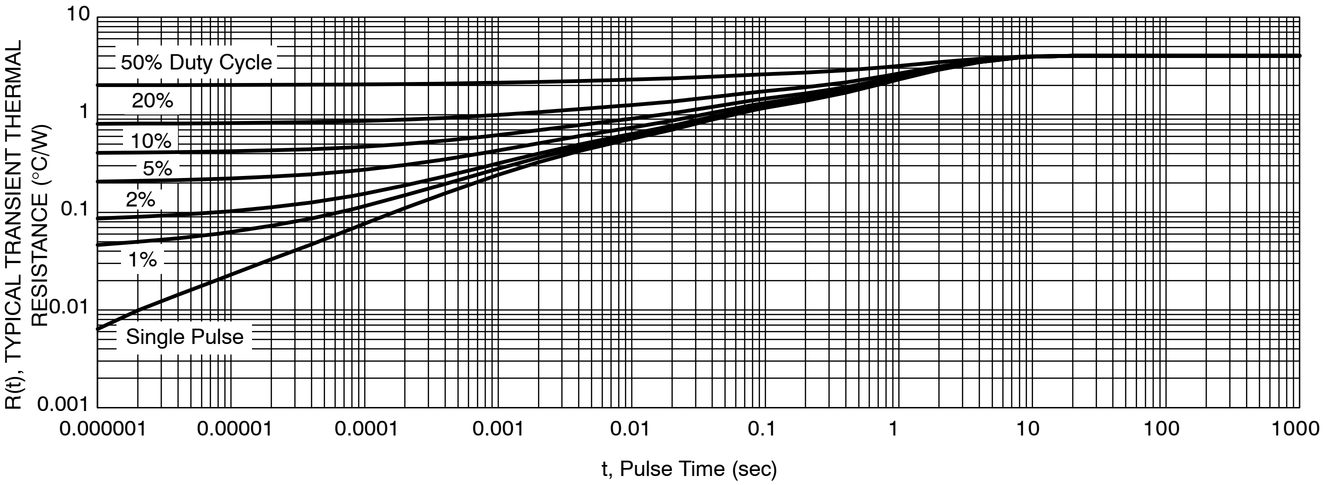


Figure 8. Typical Transient Thermal Response, Junction−to−Case for NTSJ20U100CTG

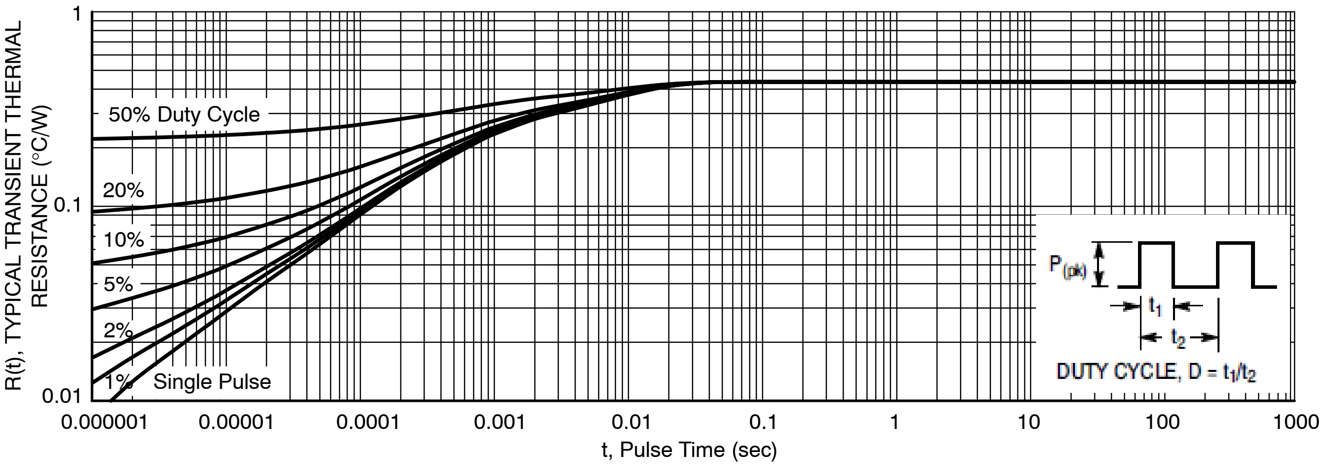
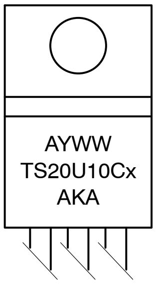


Figure 9. Typical Transient Thermal Response for NTSB20U100CTG

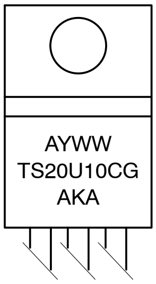
ORDERING INFORMATION

Device	Package	Shipping
NTST20U100CTG	TO−220AB (Pb−Free)	50 Units / Rail
NTSB20U100CT−1G	I^{2}PAK (Pb−Free)	50 Units / Rail
NTSJ20U100CTG	TO−220FP (Halide−Free)	50 Units / Rail
NTSB20U100CTG	D^{2}PAK (Pb−Free)	50 Units / Rail
NTSB20U100CTT4G	D^{2}PAK (Pb−Free)	800 / Tape & Reel

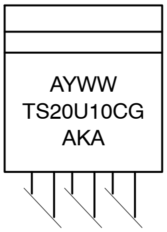
MARKING DIAGRAMS



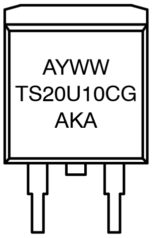
TO−220AB



TO−220FP



I^{2}PAK



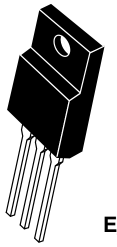
D^{2}PAK

A = Assembly Location
Y = Year
WW = Work Week
AKA = Polarity Designator
x = G or H
G = Pb−Free Package
H = Halide−Free Package

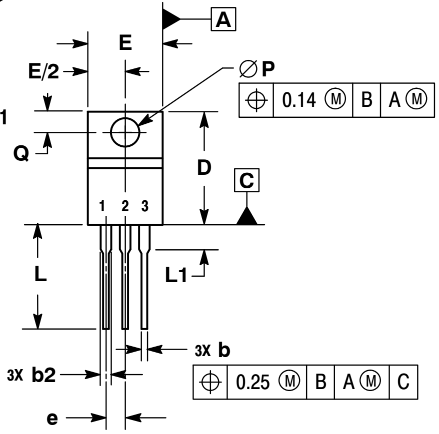
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TO−220 FULLPACK, 3−LEAD
CASE 221AH
ISSUE F

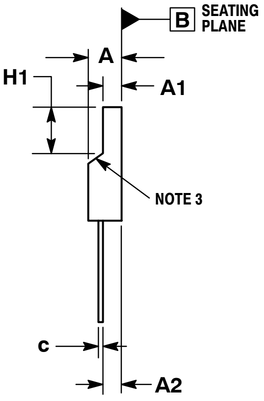
DATE 30 SEP 2014



SCALE 1:1



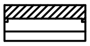
FRONT VIEW



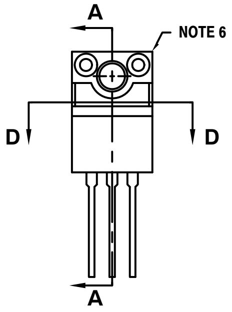
SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

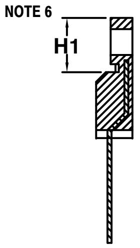
	MILLIMETERS	
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20



SECTION D−D

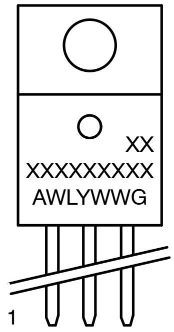


ALTERNATE CONSTRUCTION



SECTION A−A

GENERIC MARKING DIAGRAM*



A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

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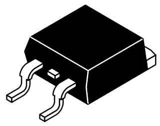
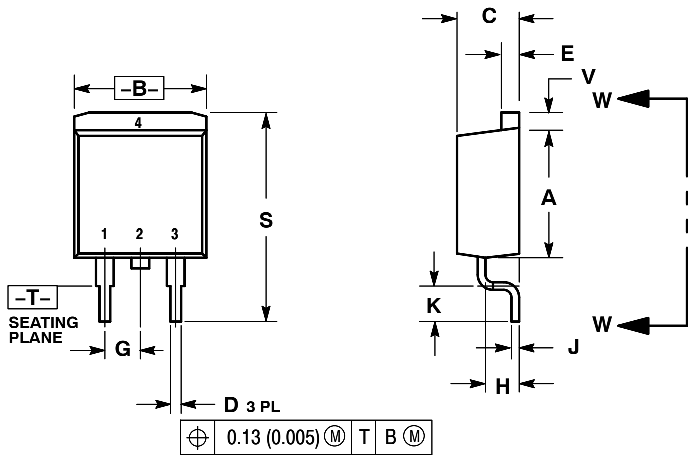


SCALE 1:1

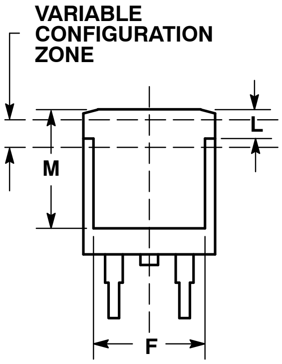
D^2PAK 3
CASE 418B−04
ISSUE L

DATE 17 FEB 2015

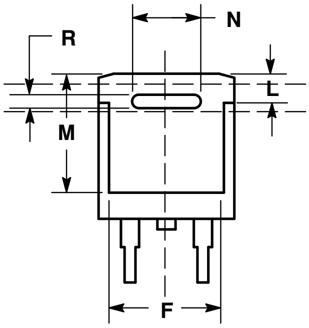


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B−01 THRU 418B−03 OBSOLETE, NEW STANDARD 418B−04.

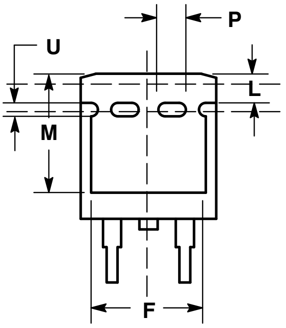
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



VIEW W−W
1



VIEW W−W
2



VIEW W−W
3

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

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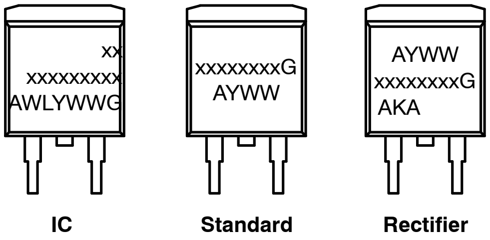
DESCRIPTION:	**D^2PAK 3**	**PAGE 1 OF 2**

D^{2}PAK 3
CASE 418B−04
ISSUE L

DATE 17 FEB 2015

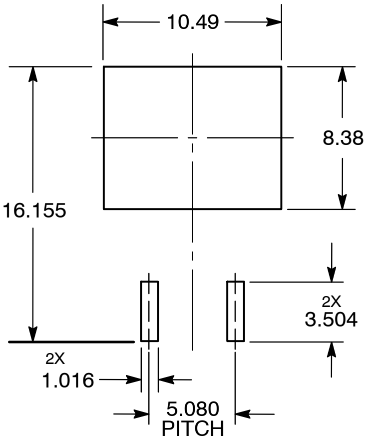
GENERIC MARKING DIAGRAM*



xx = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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